

UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/066,542	02/05/2002	Osamu Nakamura	740756-2431	5042
22204 7:	590 01/13/2006		EXAMINER	
NIXON PEABODY, LLP 401 9TH STREET, NW			JACKSON JR, JEROME	
SUITE 900			ART UNIT	PAPER NUMBER
WASHINGTON, DC 20004-2128			2815	
			DATE MAILED: 01/13/2006	6

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
Office Action Summers		10/066,542	NAKAMURA ET AL.	Chr		
•	Office Action Summary	Examiner	Art Unit			
		Jerome Jackson Jr.	2815			
Period fo	The MAILING DATE of this communication apport	pears on the cover sheet with the c	correspondence addres	s		
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPLICATION OF THE MAILING DISSION OF THE MAILING DISSION OF THE MAILING DISSION OF THE MONTHS from the mailing date of this communication. Of period for reply is specified above, the maximum statutory period or the reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing ed patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tin will apply and will expire SIX (6) MONTHS from a. cause the application to become ABANDONE	N. nely filed the mailing date of this commur D (35 U.S.C. § 133).	·		
Status						
1)[\]	Responsive to communication(s) filed on <u>07 N</u>	lovember 2005				
3)□	/ 	,—				
الــا(د	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
	closed in accordance with the practice under z	ex parte Quayle, 1955 C.D. 11, 45	DS U.G. 213.			
Dispositi	ion of Claims					
4)🖂	☑ Claim(s) <u>1,3-6,8-13,15-18,20-23,25-27 and 41-56</u> is/are pending in the application.					
	4a) Of the above claim(s) is/are withdrawn from consideration.					
5)⊠	☐ Claim(s) <u>1,3-6,8-13,15-18,20-22,25-27 and 41-44</u> is/are allowed.					
6)⊠	Claim(s) <u>23 and 45-56</u> is/are rejected.					
· <u> </u>	Claim(s) is/are objected to.					
8)□	Claim(s) are subject to restriction and/o	or election requirement.				
Applicati	on Papers	•				
	The specification is objected to by the Examine	ar.				
*	The drawing(s) filed on is/are: a) acc		Evaminer			
10)	Applicant may not request that any objection to the					
	Replacement drawing sheet(s) including the correct	• • • • • • • • • • • • • • • • • • • •		121/4)		
11)	The oath or declaration is objected to by the Ex	• • • • • • • • • • • • • • • • • • • •		, ,		
11)	The ball of declaration is objected to by the Ex	karniner. Note the attached Office	Action of form PTO-13	02.		
Priority ι	ınder 35 U.S.C. § 119					
	Acknowledgment is made of a claim for foreign All b) Some * c) None of:)-(d) or (f).			
	1. Certified copies of the priority document					
	2. Certified copies of the priority document		•			
	3. Copies of the certified copies of the prio	× •	ed in this National Stag	е		
	application from the International Bureau	· · · · · · · · · · · · · · · · · · ·				
* 5	See the attached detailed Office action for a list	of the certified copies not receive	ed.			
Attachmen	t(s)					
1) Notic	e of References Cited (PTO-892)	4) Interview Summary	(PTO-413)			
	e of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Da	ate	0.1		
	mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) r No(s)/Mail Date	6) Other:	atent Application (PTO-152)			

Application/Control Number: 10/066,542

Art Unit: 2815

Claims 1,3-6,8-13,15-18,20-22 and 41-44 are allowed.

Applicant's arguments filed 10/11/05 regarding these claims are convincing of patentability. Henley's "first portion" would include the gettering atom region which has a lower crystallinity than the "second portion" without the gettering atoms. Thus the Henley structure would not meet the claim 1 structure.

The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.

Claims 23,25-27,45-56 are rejected under 35 U.S.C. 102(b) as anticipated by or, in the alternative, under 35 U.S.C. 103(a) as obvious over Henley, of record.

The previous rejection still applies. There are no recitations in claim 23 of a channel region containing the gradient and first and second portions as in allowed claims above. The semiconductor layer of Henley meets the claimed semiconductor layer structure as previously stated. Claim 45 likewise is rejected as there are no recitations the channel region contains first and second portions as in the allowed claims. Figure 8 of Henley shows a gate structure 803 with two layers, presumably the bottom layer being a gate insulating film. In the event applicant argues that the bottom layer is not a gate insulating film, such would be considered a completely obvious design for a FET structure as Henley as insulated gate electrodes enable low gate leakage current among numerous other advantages, are widely practiced in the art and take the name "MOSFET" or "MISFET". Top or Bottom gate design is also considered obvious routine design to one of ordinary skill and would not be considered a patentable distinction over Henley without unexpected results. Claims 49 and 53 are similar to

Art Unit: 2815

claim 45 and likewise rejected. Dependent claims as stated previously recite obvious applications of thin film FET devices and are not considered by themselves patentable additions to the independent claims.

Claims 23,25-27,45-56 are rejected under 35 U.S.C. 103(a) as being unpatentable over Henley in view of Wu '833.

In regard to FET design with insulated gates, Wu shows and suggests insulated gate design with SiN insulator. Moreover, Wu suggests bottom gate design for the advantage of removing the semiconductor layer away from the glass substrate. See the backround of the invention. It would have been obvious to have practiced a thin film semiconductor layer as Henley with rare atom gettering sites to improve the semiconductor layer quality and further to have practiced bottom insulated gate design from Wu to improve FET device performance and use an advantageous two step mask process. Applicant's claims are obvious structure. Claims 49 and 53 are similar to rejected claim 23 and likewise rejected.

Applicant's arguments filed 10/11/05 have been fully considered but they are not persuasive for all claims. As stated above, arguments related to allowed claims are persuasive. Regarding rejected claim 23, there is no recitation of "channel region" with first and second portions as in allowed claim 1. Henley shows a semiconductor layer with a first portion containing rare gas gettering atoms and other portions above and below the first portion without rare gas atoms. The other portions have higher crystallinity as they do not contain the rare gas atoms. Accordingly claim 23 is rejected.

In regard to claim 45, the new rejection including Wu shows gate insulators and bottom gate design to be advantageous and obvious to practice with SOI including rare gas gettering portions as in Henley.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Jerome Jackson Jr. whose telephone number is 571-272-1730. The examiner can normally be reached on M-Th.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on 571-272-1664. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

jj

JEROME JACKSON PRIMARY EXAMINER

Page 4